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Docket Number (Optional)	Application Number
SETI-0001	09/966563
Applicant(s)	
Khan et al.	
Filing Date	Group Art Unit
September 27, 2001	2814

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

LP	"Piezoelectric and Piezoelectric Properties of GaN-Based Materials," M. S. Shur et al., MRS Internet J. Nitride Semicond. Res. 4S1, G1.6 (1999), pp. 1-12.
	"Piezoeffect and Gate Current in AlGaIn/GaN High Electron Mobility Transistors," R. Gaska et al., Applied Physics Letters, Vol. 71, No. 25, December 22, 1997, pp. 3673-3675.
	"Two-Dimensional Electron-Gas Density in AlxGa1-x/GaN Heterostructure Field-Effect Transistors," N. Maeda et al., Applied Physics Letters, Vol. 73, No. 13, September 28, 1998, pp. 1856-1858.
	"Piezoelectric Charge Densities in AlGaIn/GaN HFETs," P.M. Asbeck et al., Electronic Letters, Vol. 33, No. 14, July 3, 1997, 1230-1231.
	"Spontaneous Polarization and Piezoelectric Constants of III-V Nitrides," F. Bernardini et al., Physical Review B, Vol. 56, No. 16, October 15, 1997, pp. R10024-R10027.
	"Piezoelectric Doping and Elastic Strain Relaxation in AlGaIn-GaN Heterostructure Field Effect Transistors," A. D. Bykhovskii et al., Applied Physics Letters, Vol. 73, No. 24, December 14, 1998, pp. 3577-3579.
	"Ferroelectric Semiconductors," V. M. Fridkin, Russia (1976), p. 90 (pp. 64-65 in English version).
	"Lattice and Energy Band Engineering in AlInGaIn/GaN Heterostructures," M. A. Khan et al., Applied Physics Letters, Vol. 76, No. 9, February 28, 2000, pp. 1161-1163.
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LP	"Current/Voltage Characteristic Collapse in AlGaIn/GaN Heterostructure Insulated Gate Field Effect Transistors at High Drain Bias," M. A. Khan et al., Electronic Letters, Vol. 30, No. 25, December 8, 1994, pp. 2495-2496.

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